

Description

The ACE3401 is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and Battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

Features

- -30V/-4.0A, $R_{DS(ON)}=55\text{m}\Omega$ @ $V_{GS}=-10\text{V}$
- -30V/-3.2A, $R_{DS(ON)}=65\text{m}\Omega$ @ $V_{GS}=-4.5\text{V}$
- -30V/-1.2A, $R_{DS(ON)}=75\text{m}\Omega$ @ $V_{GS}=-2.5\text{V}$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23-3L package design

Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- Load Switch
- DSC
- LCD Display inverter

Absolute Maximum Ratings

($T_A=25^\circ\text{C}$ Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V_{DSS}	-30	V
Gate-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current ($T_J=150^\circ\text{C}$)	I_D	-40	A
		-3.2	
Pulsed Drain Current	I_{DM}	-15	A
Continuous Source Current (Diode Conduction)	I_S	-1.0	A
Power Dissipation	P_D	1.25	W
		0.8	
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55/150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^\circ\text{C}/\text{W}$

ACE

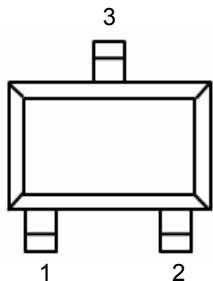
www.DataSheet4U.com

ACE3401

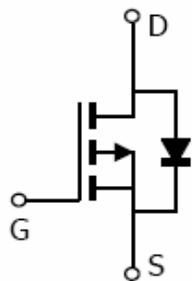
Technology P-Channel Enhancement Mode MOSFET

Packaging Type

SOT-23-3



Pin	Description
1	Gate
2	Source
3	Drain



Ordering information

Selection Guide

ACE3401 XX + H

└ Halogen - free
└ Pb - free
└ BM: SOT-23-3

ACE

Technology P-Channel Enhancement Mode MOSFET

www.DataSheet4U.com

ACE3401

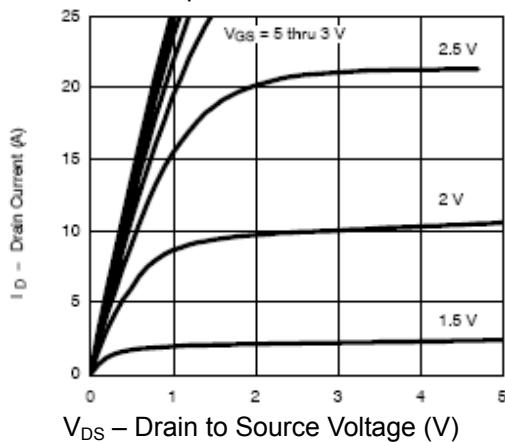
Electrical Characteristics

(TA=25°C, Unless otherwise noted)

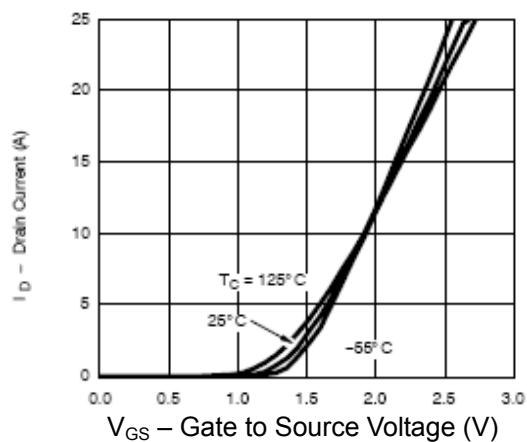
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =-250uA	-30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250uA	-0.4		-1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-24V, V _{GS} =0V			-1	uA
		V _{DS} =-24V, V _{GS} =0V T _J =55°C			-10	
On-State Drain Current	I _{D(ON)}	V _{DS} ≤-5V, V _{GS} =-10V	-10			A
Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} =-10V, I _D =-4.0A		0.045	0.055	Ω
		V _{GS} =-4.5V, I _D =-3.2A		0.050	0.065	
		V _{GS} =-2.5V, I _D =-1.2A		0.060	0.075	
Forward Transconductance	G _{fs}	V _{DS} =-5.0V, I _D =-4.0A		10		S
Diode Forward Voltage	V _{SD}	I _S =-1.0A, V _{GS} =0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =-15V, V _{GS} =-10V, I _D ≡-4.0A		14	21	nC
Gate-Source Charge	Q _{gs}			1.9		
Gate-Drain Charge	Q _{gd}			3.7		
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHz		540		pF
Output Capacitance	C _{oss}			131		
Reverse Transfer Capacitance	C _{rss}			105		
Turn-On Time	t _{d(on)}	V _{DD} =-15V, R _L =15Ω I _D ≡-1.0A, V _{GEN} =-10V R _G =6Ω		10	15	ns
	t _r			15	25	
Turn-Off Time	t _{d(off)}			31	50	
	t _r			20	30	

Typical Characteristics

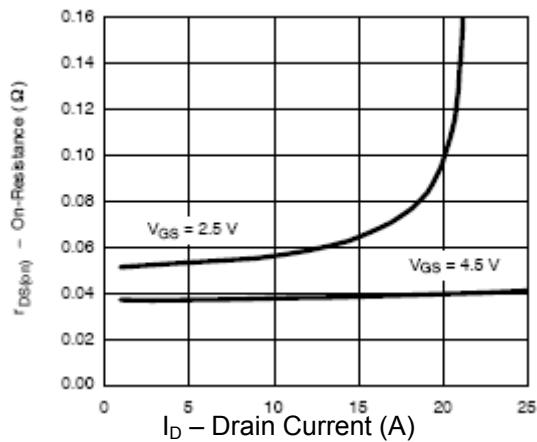
Output Characteristics



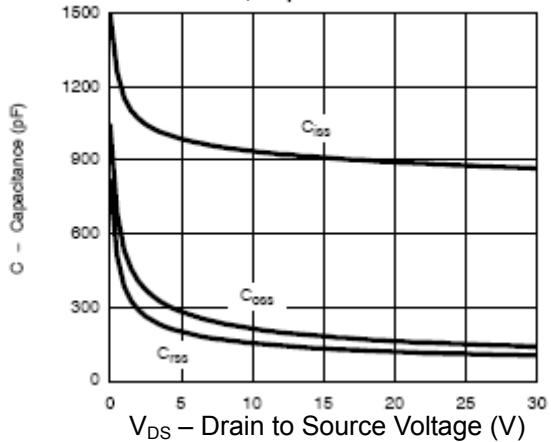
Transfer Characteristics



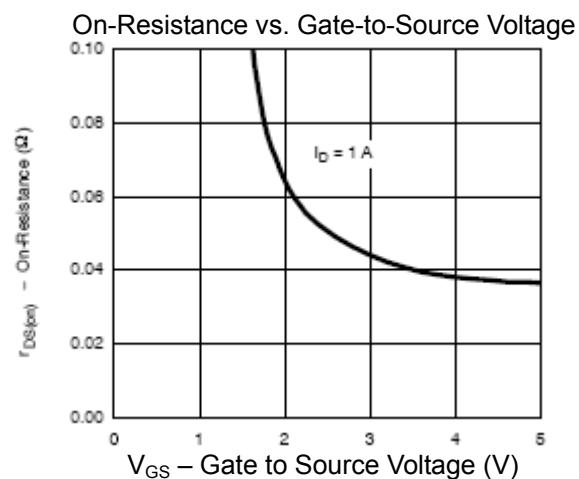
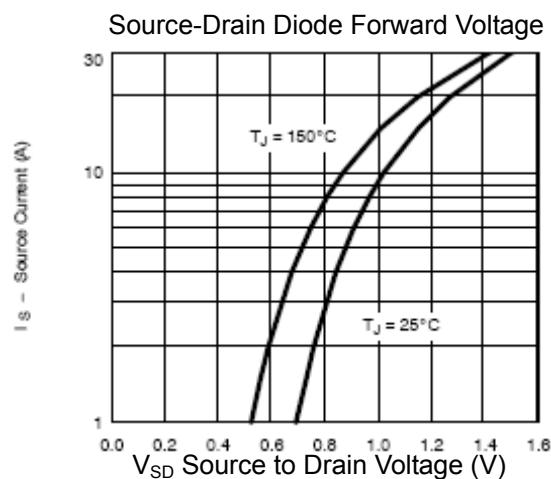
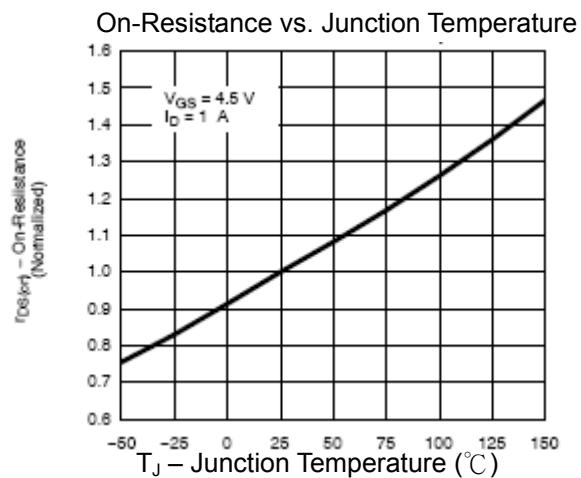
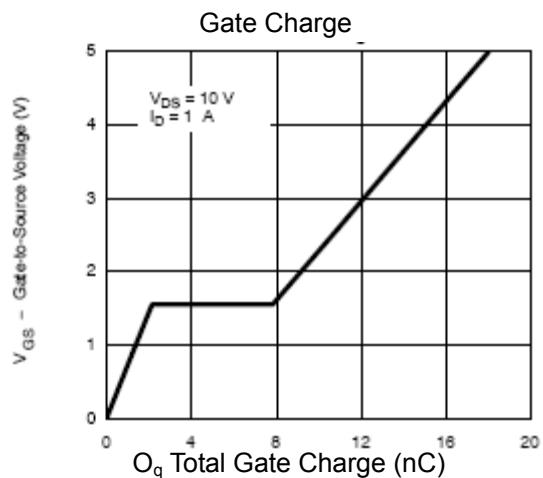
On-Resistance vs. Drain Current



Capacitance



Typical Characteristics

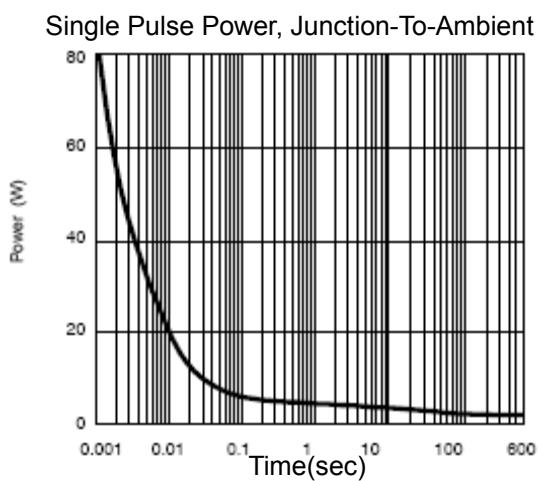
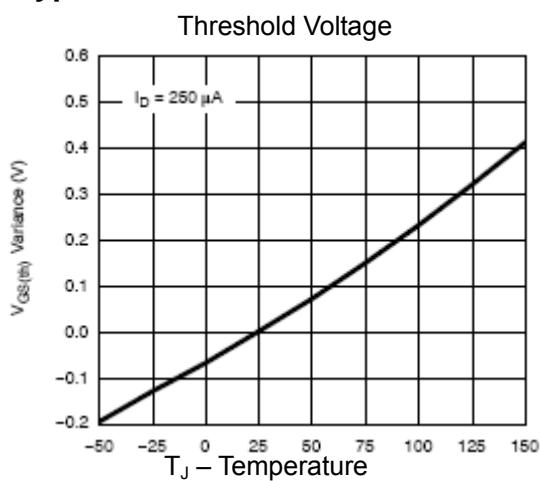


ACE

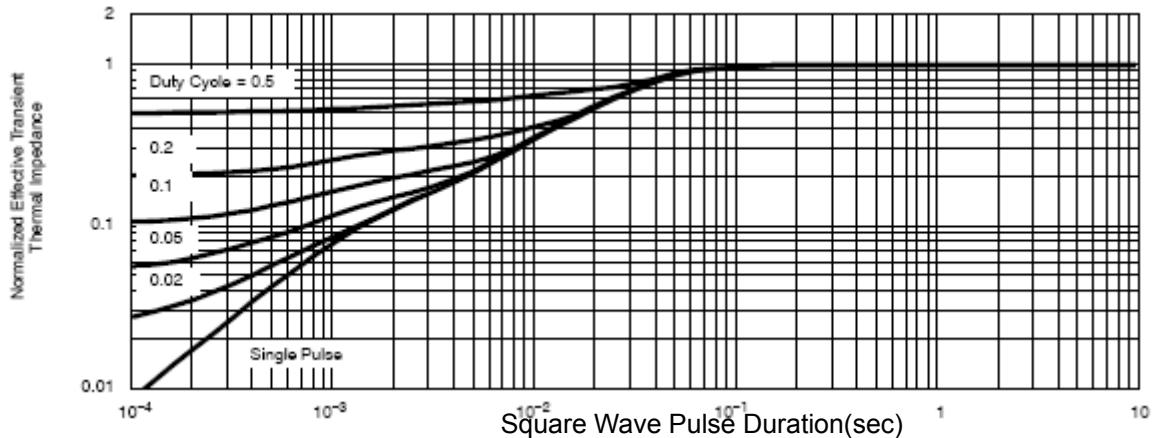
www.DataSheet4U.com ACE3401

Technology P-Channel Enhancement Mode MOSFET

Typical Characteristics



Normalized Thermal Transient Impedance, Junction-to-Foot



ACE

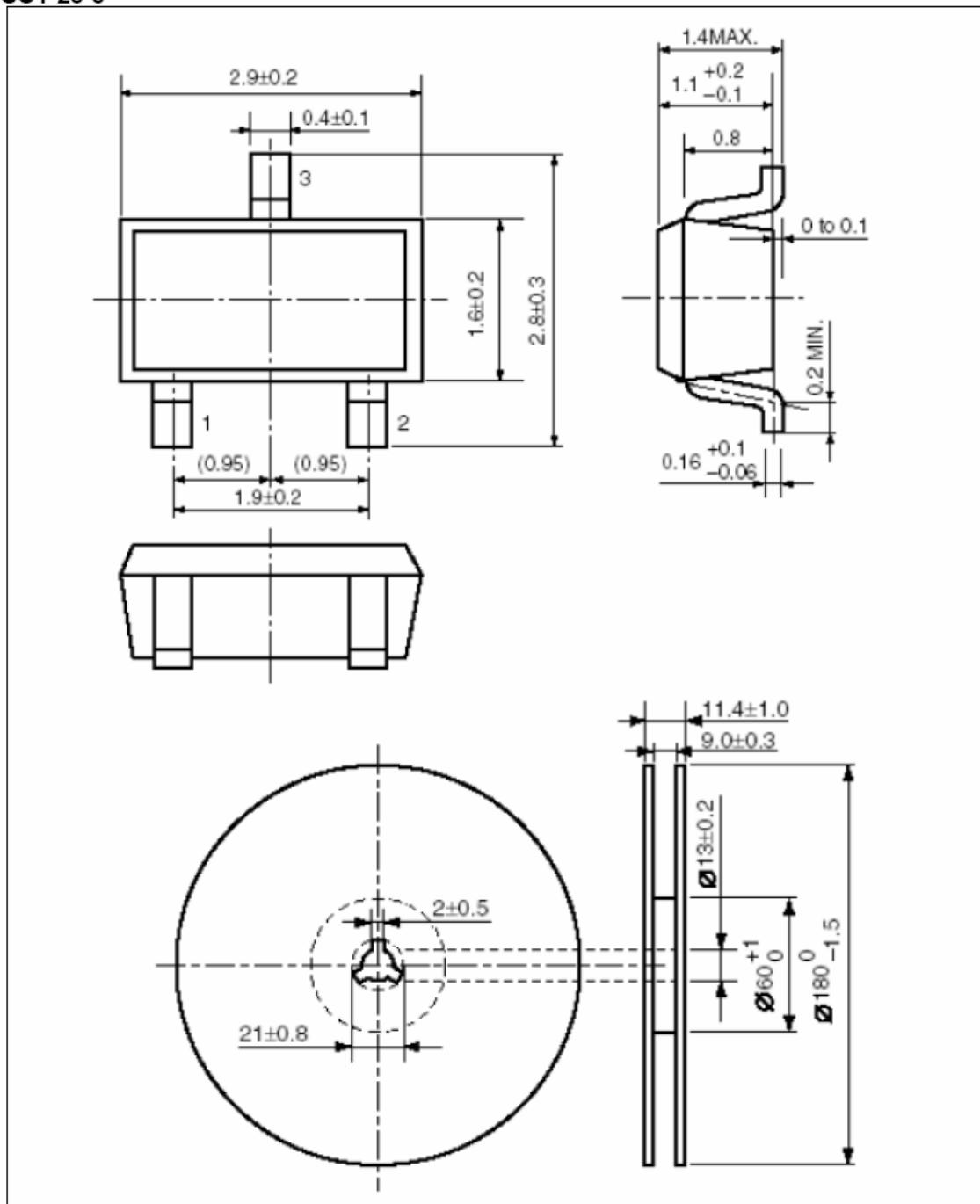
www.DataSheet4U.com

ACE3401

Technology P-Channel Enhancement Mode MOSFET

Packing Information

SOT-23-3



ACE Technology Co., LTD.
<http://www.ace-ele.com/>